

N-Channel Dual JFET



U421 – U426

FEATURES

- Ultra Low Input Bias Current 250 Fempto Amps
- Low Operating Current
- Tight Matching Characteristics

APPLICATIONS

- Ultra Low Leakage FET Input Op Amps
- Electrometer
- Infrared Detectors
- pH Meters

DESCRIPTION

The Calogic U421 Series are Dual N-Channel JFETs on a monolithic structure designed specifically for very high input impedance for differential amplification and impedance matching. This series features ultra low input bias current (250 fempto amps, U421) while offering high gain at low operating currents and tight matching characteristics. These devices are available in chip form for hybrid designs as well as a hermetic TO-78 package.

ORDERING INFORMATION

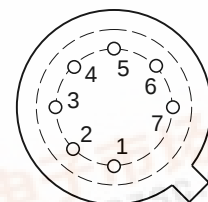
Part	Package	Temperature Range
U421-U426	TO-78 Hermetic Package	-55°C to +150°C
XU421-U426	Sorted Chips in Carriers	-55°C to +150°C

PIN CONFIGURATION



CJ4

- 1 SOURCE 1
- 2 DRAIN 1
- 3 GATE 1
- 4 CASE/BODY
- 5 SOURCE 2
- 6 DRAIN 2
- 7 GATE 2



BOTTOM VIEW

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^{\circ}\text{C}$ unless otherwise noted)

Gate-to-Gate Voltage	$\pm 40\text{V}$	Total Device Dissipation, $T_A = 25^{\circ}\text{C}$	
Gate-Drain or Gate-Source Voltage	-40V	(Derate $6.0 \text{ mW}/^{\circ}\text{C}$ to 150°C)	750 mW
Gate Current	10mA	Storage Temperature Range	-65°C to $+150^{\circ}\text{C}$
Device Dissipation (Each Side), $T_A = 25^{\circ}\text{C}$			
(Derate $3.2 \text{ mW}/^{\circ}\text{C}$ to 150°C)	400mW		

ELECTRICAL CHARACTERISTICS (25°C Unless otherwise noted)

SYMBOL	CHARACTERISTIC	U421-3			U424-6			UNIT	TEST CONDITIONS	
		MIN	TYP	MAX	MIN	TYP	MAX			
STATIC										
BV _{GSS}	Gate-Source Breakdown Voltage	-40	-60		-40	-60		V	I _G = -1μA, V _{DS} = 0	
BV _{G1G2}	Gate-Gate Breakdown Voltage	±40			±40				I _G = -1μA, I _D = 0, I _S = 0	
I _{GSS}	Gate Reverse Current ⁽¹⁾			1.0			3.0	pA	T = +25°C	V _{GS} = -20V, V _{DS} = 0
				1.0			3.0	nA	T = +125°C	
I _G	Gate Operating Current ⁽¹⁾			.25			0.5	pA	T = +25°C	V _{DG} = 10V, I _D = 30μA
				.250			-500		T = +125°C	
V _{GS (off)}	Gate-Source Cutoff Voltage	-0.4		-2.0	-0.4		-2.0	V	V _{DS} = 10V, I _D = 1nA	
V _{GS}	Gate-Source Voltage			-1.8			-2.9		V _{DG} = 10V, I _D = 30μA	
I _{DSS}	Saturation Drain Current	60		1000	60		1800	μA	V _{DS} = 10V, V _{GS} = 0	
DYNAMIC										
g _{fs}	Common-Source Forward Transconductance	300		1500	300		1500	pF	V _{DS} = 10V, V _{GS} = 0	f = 1 kHz
g _{os}	Common-Source Output Conductance			10			10			f = 1MHz
C _{iss}	Common-Source Input Capacitance			3.0			3.0			
C _{rss}	Common-Source Reverse Transfer Capacitance			1.5			1.5			
g _{fs}	Common-Source Forward Transconductance	120		350	120		350	nV/√Hz	V _{DG} = 10V, I _D = 30μA	f = 1kHz
g _{os}	Common-Source Output Conductance			3.0			3.0			f = 10Hz
ē _n	Equivalent Short Circuit Input		20	70		20	70			f = 1kHz
			10			10				f = 10 Hz R _G = 10 MΩ
NF	Noise Figure			1.0			1.0	dB		

SYMBOL	CHARACTERISTIC	U421,4			U422,5			U423,6			UNIT	TEST CONDITIONS
		MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX		
MATCH												
VGS1-VGS2	Differential Gate-Source Voltage			10			15			25	mV	V _{DG} = 10V, I _D = 30μA
$\frac{ V_{GS1}-V_{GS2} }{\Delta T}$	Differential Gate-Source Voltage Change with Temperature ⁽²⁾			10			25			40	V/ °C	V _{DG} = 10V, I _D = 30μA, T _A = -55°C, T _B = 25°C, T _C = 125°C
CMRR	Common Mode Rejection Ratio ⁽³⁾	90	95		80	90		80	90		dB	I _D = 30μA, V _{DG} = 10 to 20 V

NOTES:

1. Approximately doubles for every 10°C increase in T_A .
2. Measured at endpoints T_A , T_B and T_C .

$$3. CMRR = 20 \log_{10} \left[\frac{V_{DD}}{V_{GS1}-V_{GS2}} \right] \quad V_{DD} = 10\text{V}.$$

4. Case lead not connected.